BAV56T THRU BAV99T

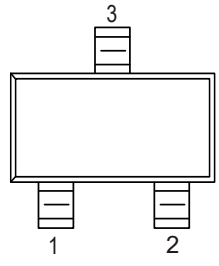
SOT-523 Plastic-Encapsulate Diodes

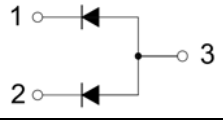
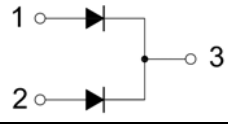
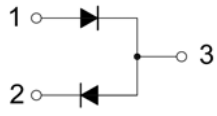
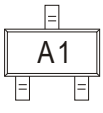
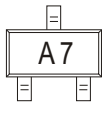
BAV56T/BAV70T/BAV99T TSWITCHING DIODE **SOT-523**

RoHS COMPLIANT

Features

- Fast Switching Speed
- For General Purpose Switching Applications
- High Conductance



BAV56T	BAV70T	BAV99T
		
MARKING:A1	MARKING:A4	MARKING:A7
		

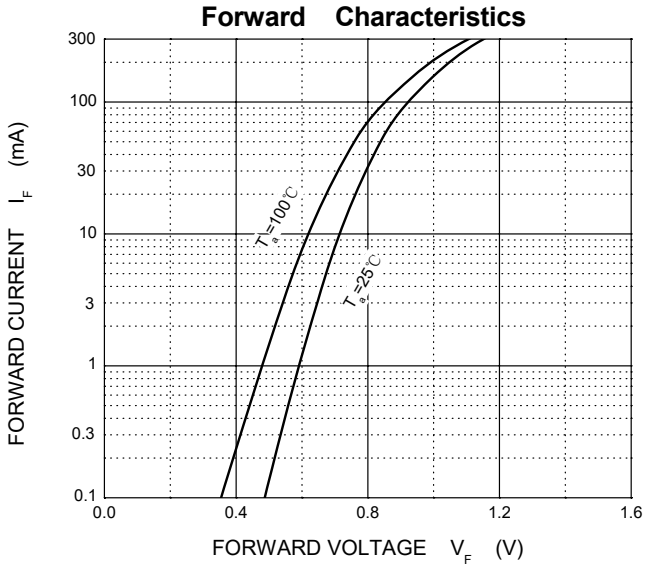
Maximum Ratings @Ta=25℃

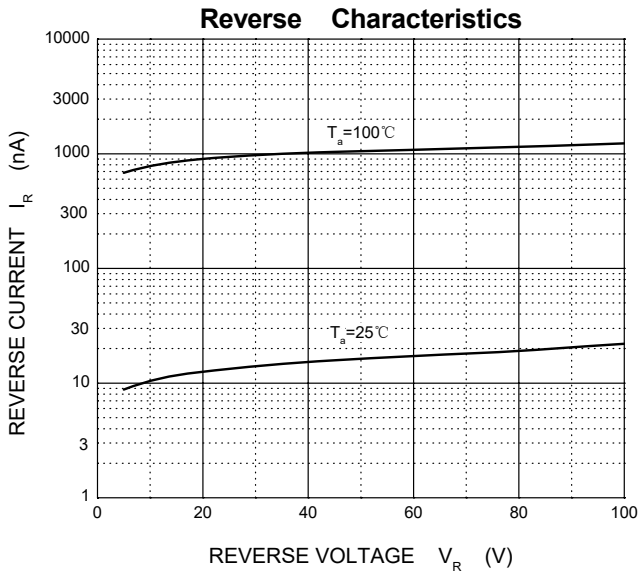
Parameter	Symbol	Limit	Unit
Reverse Voltage	V_R	85	V
Forward Current	I_F	75	mA
Non-Repetitive Peak Forward Surge Current @t=8.3ms	I_{FSM}	2.0	A
Power Dissipation	P_D	150	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	833	℃/W
Operation Junction and Storage Temperature Range	T_J,T_{STG}	-55~+150	℃

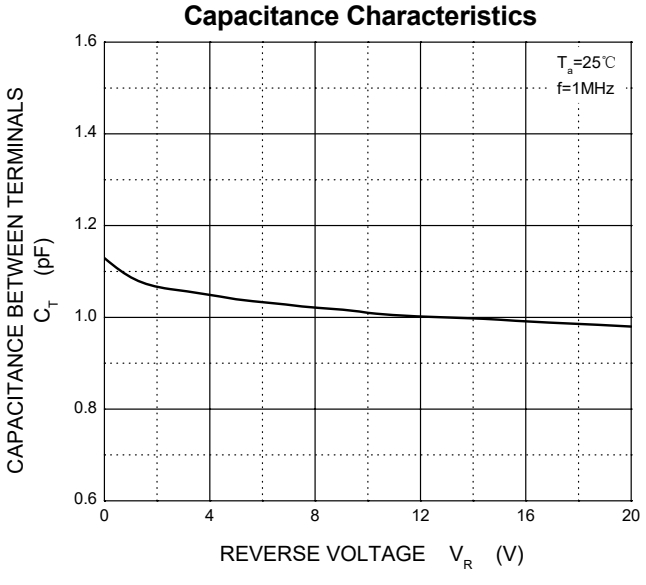
ELECTRICAL CHARACTERISTICS (Ta=25℃ unless otherwise specified)

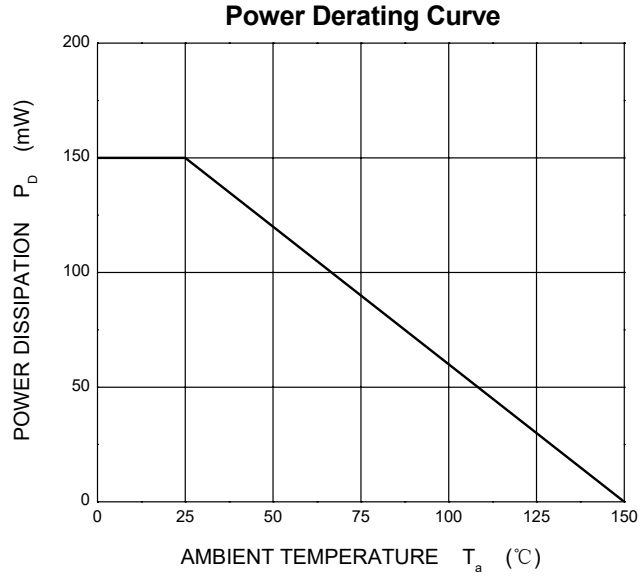
Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	$V_{(BR)}$	I_R= 1μA	85		V
Reverse voltage leakage current	I_{R1}	V_R=75V		2	μA
	I_{R2}	V_R=25V		0.03	μA
Forward voltage	V_F	I_F=1mA I_F=10mA I_F=50mA I_F=150mA		715 855 1000 1250	mV
Diode capacitance	C_D	V_R=0 f=1MHz		1.5	pF
Reverse recovery time	t_{rr}	I_F=I_R=10mA I_{rr}=0.1×I_R,R_L=100Ω		4	ns

Typical Characteristics

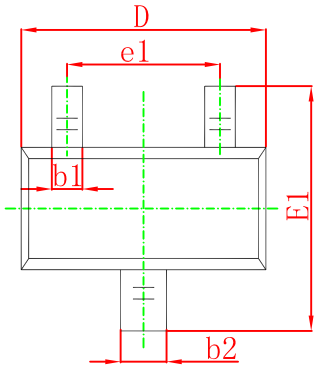


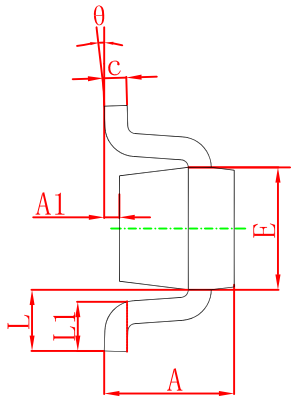


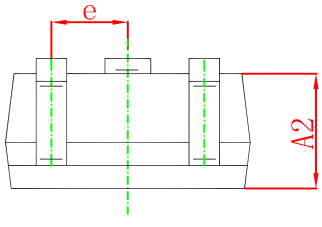




SOT-523 Package Outline Dimensions

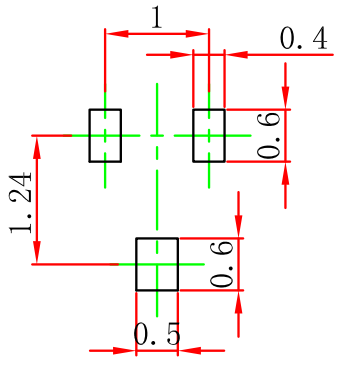






Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.600	0.950	0.024	0.037
A1	0.000	0.100	0.000	0.004
A2	0.700	0.800	0.028	0.031
b1	0.150	0.250	0.006	0.010
b2	0.150	0.350	0.006	0.014
c	0.100	0.250	0.004	0.010
D	1.400	1.800	0.055	0.071
E	0.700	0.900	0.028	0.035
E1	1.450	1.750	0.057	0.069
e	0.500 TYP.		0.020 TYP.	
e1	0.900	1.100	0.035	0.043
L	0.400 REF.		0.016 REF.	
L1	0.150	0.450	0.006	0.018
θ	0°	8°	0°	8°

SOT-523 Suggested Pad Layout



Note:

1. Controlling dimension:in/millimeters.

2. General tolerance: ±0.05mm.

3. The pad layout is for reference purposes only.